

## Ted Johansson, LIST OF PUBLICATIONS

updated 2024-02-06

### 1 REGULAR PAPERS (peer-reviewed)

1. H. Norström, S. Nygren, T. Johansson, R. Buchta, M. Östling, A. Lindberg, U. Gustafsson, C. S. Petersson, "A Refined Polycide Gate Process With Silicided Diffusions for Submicron MOS Applications", *J. Electrochem. Soc.*, 136, 805 (1989).  
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5. T. Johansson, A. Litwin, A. Ouacha, M. Willander, U. Dahlgren, "Improved UHF Power Transistors in MOSFET IC-Technology for Portable Radio Applications", *Solid State Electronics*, 37, 1983 (1994).  
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10. T. Johansson, W.-X. Ni, "Feasibility study of 25 V SiGe RF-Power Transistors for cellular base station output amplifiers", *Materials Science and Engineering B89* (2002), p. 88.  
doi:10.1016/S0921-5107(01)00763-2
11. M. Forsberg, T. Johansson, W. Liu, M. Vellaikal, "A Shallow and Deep Trench Isolation Module for RF BiCMOS", *J. Electrochem. Soc.*, 151 (12) G839-G846 (2004).  
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24. T. Johansson, R. Forchheimer and A. Åström, "Improving angle-of-view for a 1-D sensing application by using a 2-D optical sensor in "cylindrical" mode," in *IEEE Sensors Letters*, vol. 5, no. 10, pp. 1-4, Oct 2021.  
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25. P. K. B. Rangaiah, J. Engstrand, T. Johansson, M. D. Perez and R. Augustine, "92 Mb/s Fat-Intrabody Communication (Fat-IBC) With Low-Cost WLAN Hardware," in *IEEE Transactions on Biomedical Engineering*, vol. 71, no. 1, pp. 89-96, Jan. 2024.  
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50. M. F. U. Haque, T. Johansson, D. Liu, "Large Dynamic Range PWM Transmitter", presented at Gigahertz 2016 symposium, Linköping, Sweden, Mar 15-16, 2016.
51. T. Johansson, O. Najari, and M. Carlsson, "Linear CMOS-PA design in different 28 nm technologies", presented at Gigahertz 2016 symposium, Linköping, Sweden, Mar 15-16, 2016.
52. O. Morales Chacón, T. Johansson, T. Flink, "The effect of DPD bandwidth limitation on EVM for a 28 nm WLAN 802.11ac transmitter", NORCAS 2017, Linköping, Sweden, Oct 23-25, 2017. doi:10.1109/NORCHIP.2017.8124943
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57. T. Johansson, P. Rangaiah, J. Engstrand, M. Perez, and R. Augustine, "Fat-layer intra-body communication", presented at Swedish Microwave Days, Stockholm May 23-25, 2023.
58. J. Engstrand, P. Rangaiah, T. Johansson, M. Perez, R. Augustine, "Intrabody Communication Through Fat Tissue for Brain-Machine Interface Applications". presented at Medicinteknikdagarna 2023, Stockholm, Sweden, 9-11 oktober, 2023, 103-103, 2023

1. T. Johansson, "A CMOS SoC for DECT/WDCT cordless phones with 27 dBm integrated power amplifier", SSoCC'07, Fiskebäckskil, Sweden, May 14-15, 2007.
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## 5 OTHER MATERIAL

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2. T. Johansson, J. Curtis, "Gold: A Strategic Choice!", Application Note, Ericsson Components AB, 1999.
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## 6 Lic. Eng. Thesis.

T. Johansson, "Process and Device Development of MOSFET Technologies for Telecommunication Applications", Linköping Studies in Science and Technology, Thesis No. 375. Presented at LiU June 2, 1993.  
ISBN 91-7871-115-0

## 7 Ph.D. Thesis.

T. Johansson, "The transistor, with emphasis on its use for radio frequency telecommunication.", Linköping Studies in Science and Technology, Dissertation No. 508. Presented at LiU, February 13, 1998.  
ISBN 91-7219-110-4